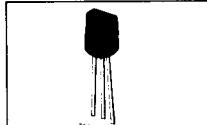


No. C268C



2SB598/2SD545

Silicon Epitaxial Planar Type Transistor
FOR AUDIO FREQUENCY POWER AMP., CONVERTERS,
ELECTRONIC GOVERNORS

The 2SB598NP/2SD545NP are complementary pair transistors that are packaged in small packages and are large in current capacity and excellent in saturation characteristic and h_{FE} linearity. In addition to the above application areas, they are also suited for use in desk-top calculator power supplies, relay drivers.

Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$

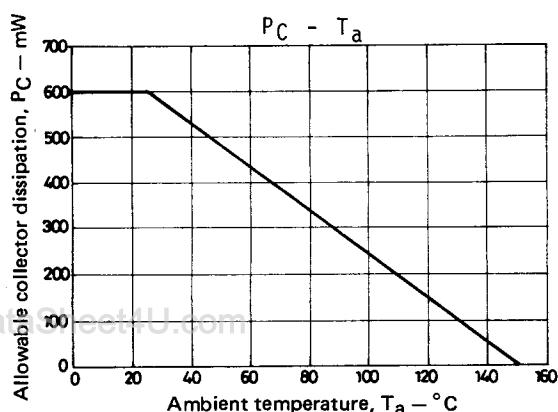
| | 2SB598 | 2SD545 | unit |
|------------------------------|-----------|------------|------------------|
| Collector to base voltage | V_{CBO} | -25 | V |
| Collector to emitter voltage | V_{CEO} | -25 | V |
| Emitter to base voltage | V_{EBO} | -5 | V |
| Collector current | I_C | -1.0 | A |
| | i_{cp} | -1.5 | A |
| Collector dissipation | P_C | 600 | mW |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 ~ +150 | $^\circ\text{C}$ |

Electrical Characteristics/ $T_a = 25^\circ\text{C}$

| | 2SB598 | 2SD545 | unit |
|---|--|--------|-------------------|
| Collector cutoff current | I_{CBO} $V_{CB} = (-)20\text{V}, I_E = 0$ | -1.0 | 1.0 μA |
| Emitter cutoff current | I_{EBO} $V_{EB} = (-)4\text{V}, I_C = 0$ | -1.0 | 1.0 μA |
| Collector to base breakdown voltage | $V_{(BR)CBO} I_C = (-)10 \mu\text{A}, I_E = 0$ | 25 | V |
| Collector to emitter breakdown voltage | $V_{(BR)CEO} I_C = (-)1 \text{ mA}, R_{BE} = \infty \Omega$ | 25 | V |
| Emitter to base breakdown voltage | $V_{(BR)EBO} I_E = (-)10 \mu\text{A}, I_C = 0$ | 5 | V |
| DC current gain | $h_{FE}(1)^*$ $V_{CE} = (-)2\text{V}, I_C = (-)50\text{mA}$ | 60 | 60 |
| | $h_{FE}(2)$ $V_{CE} = (-)2\text{V}, I_C = (-)1\text{A(pulse)}$ | 30 | 560 |
| Gain bandwidth product | f_T $V_{CE} = (-)10\text{V}, I_C = (-)50\text{mA}$ | 180 | 180 MHz |
| Common base output capacitance | c_{ob} $V_{CB} = (-)10\text{V}, f = 1 \text{ MHz}$ | 25 | 15 pF |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ $I_C = (-)500\text{mA}, I_B = (-)50\text{mA}$ | -0.15 | 0.1 V |
| Base to emitter saturation voltage | $V_{BE(sat)}$ $I_C = (-)500\text{mA}, I_B = (-)50\text{mA}$ | -0.85 | 0.85 V |
| | | -1.2 | 1.2 V |

* $h_{FE}(1)$ is classified by 2 V, 50 mA as follows:

| | | | | | | | | | | | |
|----|---|-----|-----|---|-----|-----|---|-----|-----|---|-----|
| 60 | D | 120 | 100 | E | 200 | 160 | F | 320 | 280 | G | 560 |
|----|---|-----|-----|---|-----|-----|---|-----|-----|---|-----|



Case Outline 2003
(unit: mm)

